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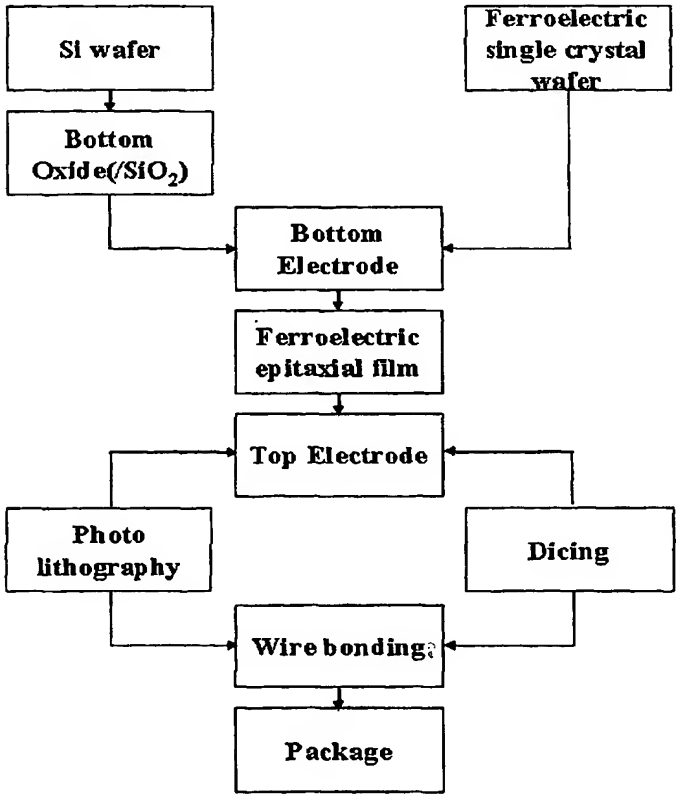
(54) Title: METHOD FOR PREPARATION OF FERROELECTRIC SINGLE CRYSTAL FILM STRUCTURE USING DEPOSITION METHOD



(57) Abstract: A film structure of a ferroelectric single crystal which can be beneficially used in the fabrication of high-performance electric and electronic parts and devices is prepared by forming an electrode layer having a perovskite crystal structure on a substrate made of a silicon or ferroelectric single crystal optionally polished to have a off-axis crystal structure, and epitaxially growing a layer of a ferroelectric single crystal thereon by pulsed laser deposition (PLD) or metallorganic chemical vapor deposition (MOCVD).

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